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**Week 3 Quiz ANSWERS Equilibrium Carrier Concentrations**

**ECE 305: Semiconductor Devices**

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Answer the **multiple choice questions** below by choosing the **one, best answer**.

- 1) Consider Si doped with Phosphorous ( $N_D \approx 10^{15} \text{ cm}^{-3}$ ,  $E_C - E_D = 0.045 \text{ eV}$ ). Where is the Fermi level located at  $T = 0 \text{ K}$ ?
  - a) Near the middle of the bandgap.
  - b) In the upper half of the bandgap.
  - c) In the lower half of the bandgap.
  - d) Below  $E_C$  and above  $E_D$ .**
  - e) Above  $E_C$ .
  
- 2) Consider Si doped with Phosphorous ( $N_D \approx 10^{15} \text{ cm}^{-3}$ ,  $E_C - E_D = 0.045 \text{ eV}$ ). Where is the Fermi level located at  $T = 300 \text{ K}$ ?
  - a) Near the middle of the bandgap.
  - b) In the upper half of the bandgap.**
  - c) In the lower half of the bandgap.
  - d) Below  $E_C$  and above  $E_D$ .
  - e) Above  $E_C$ .
  
- 3) Consider Si doped with Phosphorous ( $N_D \approx 10^{15} \text{ cm}^{-3}$ ,  $E_C - E_D = 0.045 \text{ eV}$ ). Where is the Fermi level located at  $T = 600 \text{ K}$ ? (HINT:  $n_i(600 \text{ K}) = 4 \times 10^{15} \text{ cm}^{-3}$ .)
  - a) Near the middle of the bandgap.**
  - b) In the upper half of the bandgap.
  - c) In the lower half of the bandgap.
  - d) Below  $E_C$  and above  $E_D$ .
  - e) Above  $E_C$ .
  
- 4) Which of the following is true in equilibrium?
  - a)  $n = n_i = 1/p$
  - b)  $n = N_C$
  - c)  $np = N_C N_V$
  - d)  $np = n_i^2$**
  - e)  $np = 1/n_i^2$

- 5) Which of the following is true for a non-degenerate semiconductor in equilibrium?
- $p = n_i e^{(E_F - E_V)/k_B T}$  .
  - $p = n_i e^{(E_V - E_F)/k_B T}$
  - $p = n_i e^{(E_F - E_i)/k_B T}$
  - $p = n_i e^{(E_i - E_F)/k_B T}$**
  - $p = n_i e^{(E_F + E_i)/k_B T}$
- 6) Which of the following is true for a non-degenerate semiconductor in equilibrium?
- $p = N_V e^{(E_F - E_V)/k_B T}$  .
  - $p = N_V e^{(E_V - E_F)/k_B T}$**
  - $p = N_V e^{(E_F - E_i)/k_B T}$
  - $p = N_V e^{(E_i - E_F)/k_B T}$
  - $p = N_V e^{(E_F + E_i)/k_B T}$
- 7) What is the **electron concentration** in Si at 300 K with a boron doping of  $N_A = 10^{17} \text{ cm}^{-3}$ ?
- $n = 10^{10} \text{ cm}^{-3}$
  - $n = 10^{17} \text{ cm}^{-3}$
  - $n = 10^3 \text{ cm}^{-3}$**
  - $n = 10^6 \text{ cm}^{-3}$
  - $n = 10^9 \text{ cm}^{-3}$
- 8) What is the mathematical statement of space charge neutrality?
- $n = p$  .
  - $n = N_D$  .
  - $n = N_D^+ - N_A^-$  .
  - $n + N_A^- = p + N_D^+$**
  - $n + N_A^- + p + N_D^+ = 0$
- 9) As temperature increases from 0 K to high temperature, the carrier concentration goes through three regions. In what order does the transition occur?
- intrinsic, extrinsic, freezeout
  - extrinsic, intrinsic, freezeout
  - freezeout, intrinsic, extrinsic
  - freezeout, extrinsic, intrinsic**
  - intrinsic, freezeout, extrinsic